

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
10 May 2001 (10.05.2001)

PCT

(10) International Publication Number
WO 01/33677 A3

(51) International Patent Classification?: H01S 5/343,
H01L 31/00, 33/00, 31/18, H01S 3/19

(21) International Application Number: PCT/US00/41775

(22) International Filing Date:
1 November 2000 (01.11.2000)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/162,813 1 November 1999 (01.11.1999) US

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(81) Designated States (national): CN, JP, KR, US.

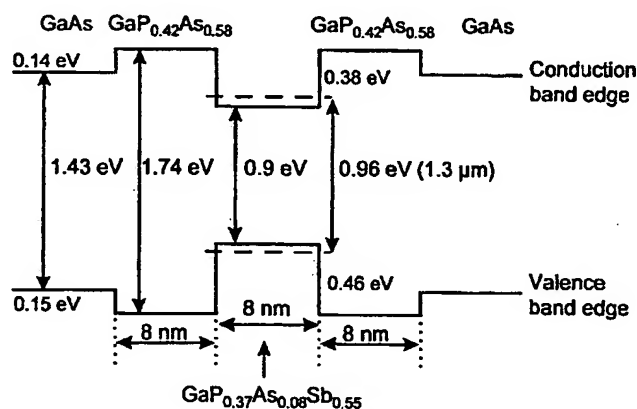
(84) Designated States (regional): European patent (AT, BE,
CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC,
NL, PT, SE, TR).

Published:
— with international search report

(88) Date of publication of the international search report:
25 October 2001

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: LONG WAVELENGTH PSEUDOMORPHIC InGaNPAsSb TYPE-I AND TYPE-II ACTIVE LAYERS FOR THE
GAAS MATERIAL SYSTEM



(57) Abstract: The invention discloses improved structures of light-processing (e.g., light-emitting and light-absorbing/sensing) devices, in particular Vertical Cavity Surface Emitting Lasers (VCSELs), such as may find use in telecommunications applications. The disclosed VSCAL devices and production methods provide for an active region having a quantum well structure grown on GaAs-containing substrates, thus providing processing compatibility for light having wavelength in the range 1.0 to 1.6 μm. The active region structure combines strain-compensating barriers with different band alignments in the quantum wells to achieve a long emission wavelength while at the same time decreasing the strain in the structure. The improved functioning of the devices disclosed results from building them with multicomponent alloy layers having a large number of constituents. The invention discloses as a key constituent in the proposed alloy layers for the active region a substance, such as nitrogen (N), suitable for reducing bandgap energy (i.e., increasing light wavelength) associated with the layers, while at the same time lowering the lattice constant associated with the structure and hence lowering strain.

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INTERNATIONAL SEARCH REPORT

In International Application No
PCT/US 00/41775

A. CLASSIFICATION OF SUBJECT MATTER

IPC 7 H01S5/343 H01L31/00 H01L33/00 H01L31/18 H01S3/19

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 7 H01S

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, PAJ, INSPEC, COMPENDEX

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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X	HAINS C P ET AL: "ROOM-TEMPERATURE PULSED OPERATION OF TRIPLE-QUANTUM-WELL GAINNAS LASERS GROWN ON MISORIENTED GAAS SUBSTRATES BY MOCVD" IEEE PHOTONICS TECHNOLOGY LETTERS, IEEE INC. NEW YORK, US, vol. 11, no. 10, October 1999 (1999-10), pages 1208-1210, XP000880896 ISSN: 1041-1135 the whole document ----- -/--	1-6, 14-23

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

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Date of the actual completion of the international search

13 July 2001

Date of mailing of the international search report

27/07/2001

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INTERNATIONAL SEARCH REPORT

In tional Application No
PCT/US 00/41775

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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INTERNATIONAL SEARCH REPORT

Information on patent family members

In ternational Application No

PCT/US 00/41775

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